

General Description

The MAX5951 is a 12V pulse-width modulated (PWM), step-down, DC-DC controller. The device operates over the input-voltage range of 8V to 16V or $5\dot{V}$ ±10%, and provides an adjustable output from 0.8V to 5.5V. The device delivers up to 10A of load current with excellent load-and-line regulation.

The MAX5951 PWM section utilizes a voltage-mode control scheme for good noise immunity and offers external compensation, allowing for maximum flexibility with a wide selection of inductor values and capacitor types. The device operates at a fixed switching frequency that is programmable from 100kHz to 1MHz and can be synchronized to an external clock signal though the SYNCIN input. The device includes undervoltage lockout (UVLO) and digital soft-start. Protection features include lossless valley-mode current limit, hiccup-mode output short-circuit protection, and thermal shutdown.

The MAX5951 is available in a space-saving 5mm x 5mm, 32-pin thin QFN package and is specified for operation over the -40°C to +85°C extended temperature range. Refer to the MAX5950 data sheet for a pincompatible PWM controller with hot swap.

Applications

PCI-e Express Modules™ General 12V or 5V Input PWM Controllers **Blade Servers RAID Base Stations**

Workstations

PCI-e Express Modules is a trademark of PCI-SIG.

Features

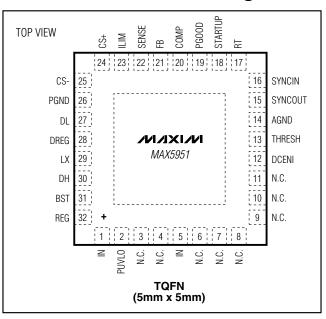
- ♦ 8V to 16V or 5V ±10% Input-Voltage Range
- **♦ Lossless Valley-Mode Current Sensing**
- ♦ Output Voltage Adjustable from 0.8V to 5.5V
- **♦ Voltage-Mode Control**
- **♦ External Compensation for Maximum Flexibility**
- ♦ Digital Soft-Start
- **♦** Sequencing or Ratiometric Tracking
- ♦ Startup Synchronization
- **♦ Programmable PGOOD Output**
- ♦ Programmable Switching Frequency from 100kHz to 1MHz
- **♦** External Frequency Synchronization
- ♦ SYNCIN and SYNCOUT Enable 180° Out-of-Phase Operation
- **♦** Thermal Shutdown and Short-Circuit Protection
- ♦ Space-Saving, 5mm x 5mm, 32-Pin TQFN Package

Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	PKG CODE
MAX5951ETJ+	-40°C to +85°C	32 TQFN	T3255-4

⁺Denotes lead-free package.

Pin Configuration



ABSOLUTE MAXIMUM RATINGS

IN to AGNDBST to AGND	0.3V to +30V
BST to LX	
CS- to AGND	· · · · · /
REG, DREG, PUVLO, DCENI, SYNCIN,	- ,
SENSE to AGND	
RT, ILIM, STARTUP, PGOOD, FB, CS+	
SYNCOUT, COMP to AGND	
DL to PGND	0.3V to (V _{DREG} + 6V)
DH to LX	0.3V to (V _{BST} + $0.3V$)
PGND to AGND	0.3V to +0.3V
Input Current (any pin)	±50mA

Continuous Power Dissipation (T _A = +70°C	C)
32-Pin TQFN (derate 34.5 mW/°C above	e +70°C) .2758.6mW
32-Pin TQFN (θ_{JA})	
32-Pin TQFN (θ_{JC})	+2.1°C/W
Operating Ambient Temperature Range	
Maximum Junction Temperature	+150°C
Storage Temperature Range	
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN}=12V \text{ or } V_{IN}=V_{REG}=5V, V_{DREG}=V_{REG}, V_{PGND}=0V, V_{SYNCIN}=0V, R_{RT}=100k\Omega, R_{ILIM}=60k\Omega, C_{REG}=2.2\mu F, T_A=T_J=-40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.}$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Innut Valtage Dange	V		8		16	V
Input-Voltage Range	V _{IN}	V _{IN} = V _{REG} = V _{DREG} (Note 2)	4.5		5.5	V
Standby Supply Current		V _{IN} = 16V, V _{PUVLO} = 0V		0.3	0.5	mA
Quiescent Supply Current		$V_{IN} = 16V, V_{FB} = 0.9V$		1.6	2.6	mA
Switching Supply Current		$V_{IN} = 16V$, $V_{FB} = 0V$		5.0	8.0	mA
PWM UVLO						
Default PWM Undervoltage Lockout Threshold		V _{IN} rising	6.7		7.3	V
PWM Undervoltage Lockout Hysteresis				0.7		V
PUVLO Threshold	V _{PUVLO}	V _{PUVLO} rising	1.202	1.220	1.238	V
PUVLO Hysteresis				122		mV
PUVLO Input Impedance			180	310	500	kΩ
PWM DCENI CONTROL						
DCENI Comparator Input Common-Mode Range			0		3	V
DCENI Comparator Offset		VDCENI - VTHRESH	-10		+10	mV
DCENI Comparator Hysteresis				100		mV
DCENI Input Current			-1		+1	μΑ
THRESH Operating Voltage Range			0.6		2.5	V
TUDECH Input Current		V _{THRESH} > 0.6V	-1.5		+1	
THRESH Input Current		V _{THRESH} < 0.3V	-5		+1	μA
Default DCENI Threshold		V _{THRESH} < 0.3V	1.202	1.22	1.238	V

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN}=12V \text{ or } V_{IN}=V_{REG}=5V, V_{DREG}=V_{REG}, V_{PGND}=0V, V_{SYNCIN}=0V, R_{RT}=100k\Omega, R_{ILIM}=60k\Omega, C_{REG}=2.2\mu F, T_A=T_J=-40^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A=T_J=+25^{\circ}C$.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	S	MIN	TYP	MAX	UNITS
PWM PGOOD OUTPUT	•						•
SENSE Threshold		V _{SENSE} rising		788	800	812	mV
SENSE Hysteresis					100		mV
SENSE Input Bias Current				-1		+1	μΑ
PGOOD Internal Pullup Current					10		μΑ
PGOOD Output Voltage Low		I _{PGOOD} = -2.4mA				50	mV
INTERNAL VOLTAGE REGULAT	OR						
Output Voltage Set Point	VREG			4.7		5.3	V
Line Regulation		V _{IN} = 8V to 16V				1	mV/V
Load Regulation		IREG = 0 to 50mA				150	mV
PWM OSCILLATOR							
Oscillator Frequency Range	fsw	VSYNCIN = 0V, fsw = 5 x 10	¹⁰ / R _{RT} Hz	100		1000	kHz
		T T .0500	fsw < 500kHz	-2.5		+2.5	0/
		$T_A = T_J = +25^{\circ}C$	fsw > 500kHz	-4		+4	%
Oscillator Accuracy		T T 4000 L 0500	fsw < 500kHz	-3.5		+3.5	0/
		$T_A = T_J = -40$ °C to $+85$ °C	fsw > 500kHz	-5		+5	%
RT Voltage	V _{RT}	$50k\Omega < R_{RT} < 500k\Omega$			2		V
Maximum Duty Cycle		V _{SYNCIN} = 0V, V _{IN} = 12V		82	88		%
SYNCIN High-Level Voltage				2.1			V
SYNCIN Low-Level Voltage						0.8	V
SYNCIN Pulldown Resistor				50	100	150	kΩ
SYNCIN Rising to SYNCOUT Falling Delay					10		ns
SYNCIN Falling to SYNCOUT Rising Delay					30		ns
Maximum SYNCIN Frequency				1			MHz
SYNCOUT Voltage High	VHSYNCOUT	ISYNCOUT = +1.2mA		V _{REG} - 0.1			V
SYNCOUT Voltage Low	VLSYNCOUT	ISYNCOUT = -2.4mA				50	mV
PWM ERROR AMPLIFIER	1						
FB Input Range				0		V _{REF}	V
FB Input Current				-250		+250	nA
COMP Output Voltage Range		ICOMP = -500μA to +500μA		0.25		V _{REG} - 0.5	V
Open-Loop Gain					80		dB
Unity-Gain Bandwidth	f _{GBW}				2.5		MHz
Reference Voltage	V _{REF}	I _{COMP} = -500μA to +500μA		792	800	808	mV
	ı	1		1			1

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN}=12V \text{ or } V_{IN}=V_{REG}=5V, V_{DREG}=V_{REG}, V_{PGND}=0V, V_{SYNCIN}=0V, R_{RT}=100k\Omega, R_{ILIM}=60k\Omega, C_{REG}=2.2\mu F, T_A=T_J=-40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted. Typical values are at } T_A=T_J=+25^{\circ}C.) \text{ (Note 1)}$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
PWM COMPARATOR						
Comparator Offset Voltage				0.3		V
Comparator Propagation Delay				40		ns
PWM DIGITAL SOFT-START						
Soft-Start Duration				1024		Clocks
Deference Veltage Stone				128		Steps
Reference Voltage Steps				6.3		mV
PWM RAMP GENERATOR						
Ramp Amplitude				1.8		V
PWM CURRENT-LIMIT COMPARA	ATOR AND H	ICCUP MODE				
Cycle-by-Cycle Valley Current- Limit Threshold Adjustment Range		Limit = V _{ILIM} / 10	50		350	mV
Cycle-by-Cycle Valley Current-		$V_{ILIM} = 0.5V$	44.5		55.5	
Limit Threshold Tolerance		V _{ILIM} = 3.5V	330		366	mV
ILIM Reference Current		$V_{ILIM} = 0 \text{ to } 3.5V, T_A = T_J = +25^{\circ}C$	19	20	21	μΑ
ILIM Reference Current Tempco				3333		ppm/°C
CS+, CS- Input Bias Current		$V_{CS+} = 0V$, $V_{CS-} = -0.3V$, current out of the CS_{-}	-1		+20	μΑ
PWM HICCUP MODE	•					•
Number of Cumulative Current- Limit Events to Hiccup	N _{CL}			8		Clocks
Number of Consecutive Noncurrent-Limit Cycles to Clear NCL	NCLR			3		Clocks
Hiccup Timeout	N _H T			512		Clocks
PWM STARTUP INPUT						
STARTUP Threshold	V _{SUT}		1.1		1.9	V
STARTUP Threshold Hysteresis				250		mV
Internal Pullup Current	ISTART			10		μΑ
STARTUP Output Voltage Low		ISTARTUP = -2.4mA			0.1	V
PWM DH DRIVER						
Peak Source Current		V _{DH,LX} = 0V, pulse width < 100ns, V _{BST,LX} = 5V		2		А
Peak Sink Current		V _{DH,LX} = 5V, pulse width < 100ns, V _{BST,LX} = 5V		2		А
DH Resistance Sourcing		$I_{DH} = 50$ mA, $V_{BST,LX} = 5V$		1	3	Ω
DH Resistance Sinking		$I_{DH} = -50 \text{mA}, V_{BST,LX} = 5 \text{V}$		1	3	Ω

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN}=12V \text{ or } V_{IN}=V_{REG}=5V, V_{DREG}=V_{REG}, V_{PGND}=0V, V_{SYNCIN}=0V, R_{RT}=100k\Omega, R_{ILIM}=60k\Omega, C_{REG}=2.2\mu F, T_A=T_J=-40^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A=T_J=+25^{\circ}C$.) (Note 1)

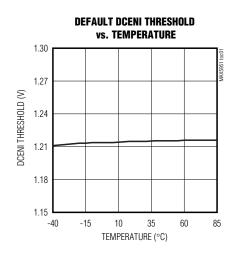
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
PWM DL DRIVER						
Peak Source Current		V _{DL} = 0V, pulse width < 100ns, V _{DREG} = 5V		2		А
Peak Sink Current		V _{DL} = 5V, pulse width < 100ns, V _{DREG} = 5V		2		А
DL Resistance Sourcing		I _{DL} = 50mA, V _{DREG} = 5V		1	3	Ω
DL Resistance Sinking		I _{DL} = -50mA, V _{DREG} = 5V		1	3	Ω
Break-Before-Make Time				25		ns
THERMAL SHUTDOWN						
Thermal Shutdown Temperature		T _J rising		135		°C
Thermal Shutdown Hysteresis				15		°C

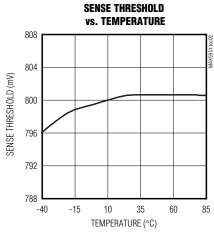
Note 1: Limits at -40°C are guaranteed by design and are not production tested.

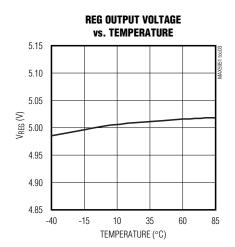
Note 2: For 5V applications, connect REG directly to IN.

Typical Operating Characteristics

 $(\textit{Typical Operating Circuits}. \ V_{IN} = 12 V \ \text{or} \ V_{IN} = V_{REG} = 5 V, \ V_{DREG} = V_{REG}, \ V_{PGND} = 0 V, \ V_{SYNCIN} = 0 V, \ R_{RT} = 49.9 k\Omega, \ R_{ILIM} = 48.7 k\Omega, \ C_{REG} = 2.2 \mu F, \ T_{A} = +25 ^{\circ} C.)$

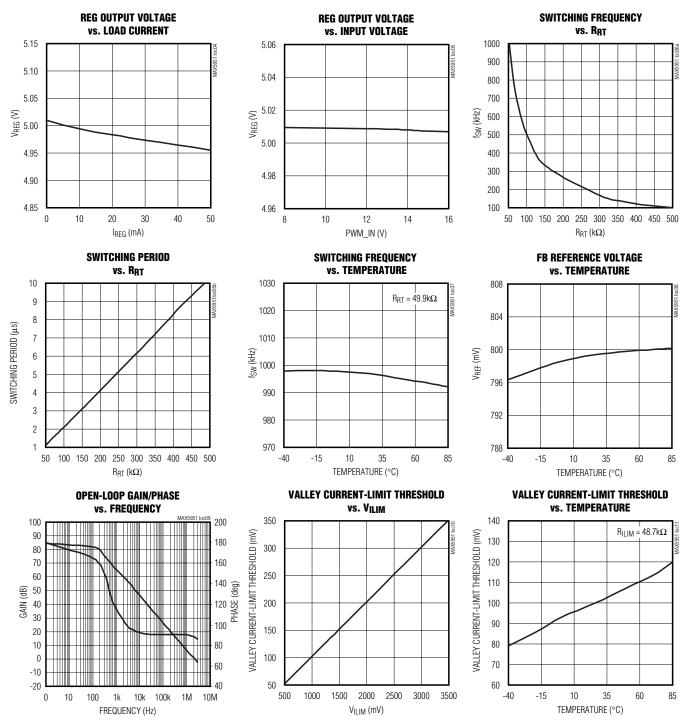






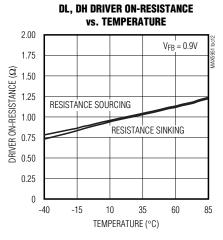
Typical Operating Characteristics (continued)

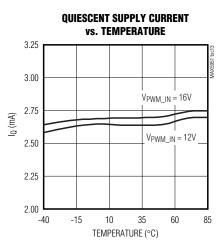
(Typical Operating Circuits. $V_{IN} = 12V$ or $V_{IN} = V_{REG} = 5V$, $V_{DREG} = V_{REG}$, $V_{PGND} = 0V$, $V_{SYNCIN} = 0V$, $V_{RT} = 49.9k\Omega$, $V_{RT} = 48.7k\Omega$, $V_{REG} = 2.2\mu F$

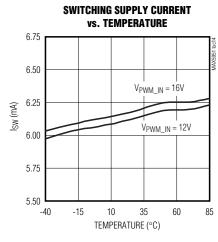


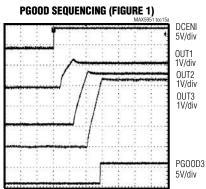
Typical Operating Characteristics (continued)

(Typical Operating Circuits. V_{IN} = 12V or V_{IN} = V_{REG} = 5V, V_{DREG} = V_{REG}, V_{PGND} = 0V, V_{SYNCIN} = 0V, R_{RT} = 49.9kΩ, R_{ILIM} = 48.7kΩ, $C_{REG} = 2.2 \mu F, T_A = +25 ^{\circ}C.$





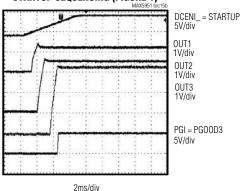




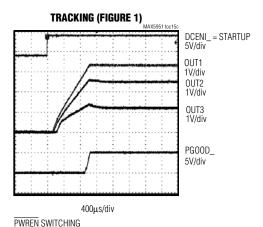


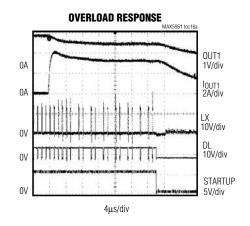
FROM HIGH TO LOW





PWREN SWITCHING FROM HIGH TO LOW

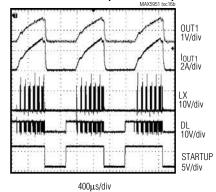




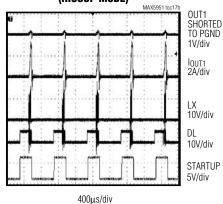
Typical Operating Characteristics (continued)

(Typical Operating Circuits. $V_{IN} = 12V$ or $V_{IN} = V_{REG} = 5V$, $V_{DREG} = V_{REG}$, $V_{PGND} = 0V$, $V_{SYNCIN} = 0V$, $V_{RRT} = 49.9k\Omega$, $V_{RRT} = 48.7k\Omega$, $V_{RRG} = 2.2\mu$ F, $V_{RRT} = 49.9k\Omega$.

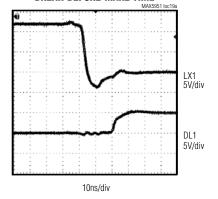
OVERLOAD RESPONSE (HICCUP MODE)



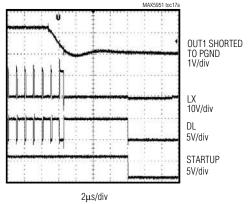
SHORT-CIRCUIT RESPONSE (HICCUP MODE)



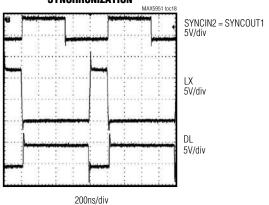
BREAK-BEFORE-MAKE TIME



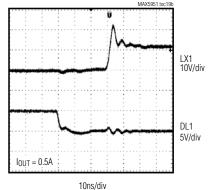
SHORT-CIRCUIT RESPONSE



SYNCHRONIZATION

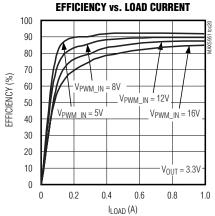


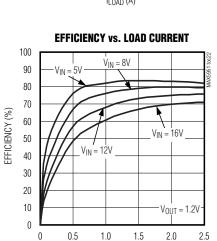
BREAK-BEFORE-MAKE TIME



Typical Operating Characteristics (continued)

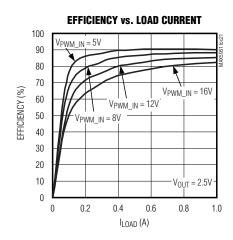
(Typical Operating Circuits. V_{IN} = 12V or V_{IN} = V_{REG} = 5V, V_{DREG} = V_{REG}, V_{PGND} = 0V, V_{SYNCIN} = 0V, R_{RT} = 49.9kΩ, R_{ILIM} = 48.7kΩ, $C_{REG} = 2.2 \mu F, T_A = +25 ^{\circ}C.$

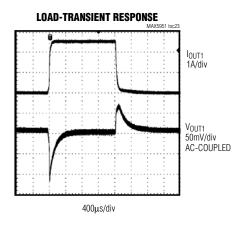


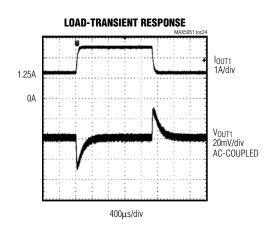


ILOAD (A)

2.0







Pin Description

PIN	NAME	FUNCTION
1, 5	IN	Supply Input Connection. Connect to an external voltage source from 8V to 16V. For 5V input application, connect IN = REG to a 5V ±10% source. Connect an external divider from IN to PUVLO to AGND to lower the startup voltage.
2	PUVLO	PWM UVLO Divider Center Point. Use an external divider to override the internal PWM UVLO divider. The rising threshold is set to 1.220V with 122mV hysteresis. Leave PUVLO unconnected for the default PWM UVLO.
3, 4, 6–11	N.C.	No Connection. Do not connect.
12	DCENI	DC-DC Enable Input. DCENI must be above V _{THRESH} for the PWM controller to start. Connect to REG if not used.
13	THRESH	DC-DC Enable Input Threshold Set. Connect a resistive divider from REG to THRESH to AGND to set the DCENI threshold. Connect to ground for a default threshold of 1.220V.
14	AGND	Analog Ground Connection. Solder the exposed pad to a large AGND plane. Connect AGND and PGND together at one point near the input bypass capacitor return terminal.
15	SYNCOUT	Synchronization Output. SYNCOUT is a synchronization signal to drive the SYNCIN of a second MAX5950 or MAX5951, if used. Leave SYNCOUT unconnected when not used.
16	SYNCIN	Synchronization Input. SYNCIN accepts the SYNCOUT from another MAX5950 or MAX5951 and shifts switching by 180°, allowing the reduction of the input bypass capacitors. When used, drive with a frequency at least 20% higher than the frequency programmed through the RT pin. If phase staggering is desired, use 50% duty cycle. Connect SYNCIN to AGND when not used.
17	RT	Oscillator Timing Resistor Connection. Connect a $500 k\Omega$ to $50 k\Omega$ resistor from RT to AGND to program the switching frequency from 100kHz to 1MHz.
18	STARTUP	Startup Input. STARTUP coordinates simultaneous soft-start for multiple converters. See the <i>Tracking (STARTUP)</i> section.
19	PGOOD	Power-Good Output. PGOOD output goes high when SENSE is above V _{REF} and STARTUP is high.
20	COMP	Error-Amplifier Output. Connect COMP to the compensation feedback network.
21	FB	Feedback Regulation Point. Connect to the center tap of a resistive divider from the converter output to AGND to set the output voltage. The FB voltage regulates to the reference voltage.
22	SENSE	Output Voltage Sense. Connect a resistive divider from the converter output to SENSE to AGND to monitor the programmed output voltage. SENSE is compared to the internal reference, V _{REF} .
23	ILIM	Valley Current-Limit Set Output. Connect a $25k\Omega$ to $175k\Omega$ resistor, R_{ILIM} , from ILIM to AGND to program the valley current-limit threshold from 50mV to 350mV. ILIM sources 20 μ A out to R_{ILIM} . The resulting voltage divided by 10 is the valley current limit. Alternatively, a resistive divider from REG to ILIM to AGND can be used to set the valley current limit.

Pin Description (continued)

PIN	NAME	FUNCTION
24	CS+	Positive Current-Sense Input. Connect CS+ to the synchronous MOSFET source (connected to PGND).
25	CS-	Negative Current-Sense Input. Connect CS- to the synchronous MOSFET drain (connected to LX).
26	PGND	Power-Ground Connection. Connect the input filter capacitor's negative terminal, the source of the synchronous MOSFET, and the output filter capacitor's return to PGND. Connect externally to AGND at a single point near the input capacitor return terminal.
27	DL	Low-Side Gate-Driver Output. DL is the gate-driver output for the synchronous MOSFET.
28	DREG	Gate-Drive Supply for the Low-Side MOSFET Driver. Connect externally to REG and the anode of the boost diode.
29	LX	Source Connection of the High-Side MOSFET and Drain Connection of the Synchronous MOSFET. Connect the inductor and the negative side of the boost capacitor to LX.
30	DH	High-Side Gate-Driver Output. DH drives the gate of the high-side MOSFET.
31	BST	High-Side Gate-Driver Supply. Connect BST to the cathode of the boost diode and to the positive terminal of the boost capacitor.
32	REG	5V Regulator Output. Bypass with a 2.2µF ceramic capacitor to AGND.
EP	EP	Exposed Pad. Connect the exposed pad to AGND.

Detailed Description

The MAX5951 is a PWM, step-down, DC-DC controller. The device operates over the input-voltage range of 8V to 16V or 5V $\pm10\%$ (VIN = VREG) and provides an adjustable output from 0.8V to 5.5V. The device delivers up to 10A of load current with excellent load-and-line regulation.

The MAX5951 PWM controller utilizes a voltage-mode control scheme for good noise immunity and offers external compensation allowing for maximum flexibility with a wide selection of inductor values and capacitor types. The device operates at a fixed switching frequency that is programmable from 100kHz to 1MHz and can be synchronized to an external clock signal through the SYNC input. The device includes UVLO and digital soft-start. Protection features include valley-mode current limit, hiccup-mode output short-circuit protection, and thermal shutdown.

PWM Controller

PWM UVLO

VIN must exceed the default PWM UVLO threshold (7V typ) before any PWM operation can commence. The UVLO circuitry keeps the MOSFET drivers, oscillator, and all the internal circuitry shut down to reduce current consumption.

Override the internal PWM UVLO divider by connecting an external resistive divider from IN to PUVLO to AGND. The PUVLO threshold is 1.220V with 122mV hysteresis.

Digital Soft-Start

The MAX5951 soft-start feature allows the load voltage to ramp up in a controlled manner, eliminating output voltage overshoot. Soft-start begins after $V_{\rm IN}$ exceeds the UVLO threshold. The soft-start circuitry gradually ramps up the reference voltage. This controls the rate of rise of the output voltage and reduces input surge currents during startup. The soft-start duration is 1024 clock cycles. The output voltage is incremented through 128 equal steps. The output reaches regulation when soft-start is completed, regardless of output capacitance and load.

Internal Linear Regulator (REG)

REG is the output terminal of a 5V LDO, which is powered from IN and provides power to the IC. Bypass REG to AGND with a 2.2µF ceramic capacitor. Place the capacitor physically close to the MAX5951 to provide good bypassing. REG is intended for powering only the internal circuitry and should not be used to supply power to external loads.

Low-Side MOSFET Driver Supply (DREG)

DREG is the supply input for the low-side MOSFET driver. Connect DREG to REG externally. Adding an RC filter (5Ω resistor and 2.2µF ceramic capacitor) from REG to DREG filters out the high peak currents of the MOSFET drivers.

High-Side MOSFET Driver Supply (BST)

BST supplies the power for the high-side MOSFET drivers. Connect the bootstrap diode from BST to DREG (anode at DREG and cathode at BST). Connect a bootstrap 1µF ceramic capacitor between BST and LX.

MOSFET Gate Drivers (DH, DL)

The high-side (DH) and low-side (DL) drivers drive the gates of the external n-channel MOSFETs. The drivers' 2A peak source-and-sink current capability provides ample drive to ensure fast rise and fall times of the switching MOSFETs. Short rise and fall times minimize switching losses. For low output-voltage applications where the duty cycle is less than 50%, choose a high-side MOSFET (Q2) with a moderate RDS(ON). Choose a low-side MOSFET (Q1) with a very low RDS(ON).

The gate driver circuitry also provides a break-beforemake time (25ns, typ) to prevent shoot-through currents during transition.

Oscillator/Synchronization Input (SYNCIN)/ Synchronization Output (SYNCOUT)

Use an external resistor at RT to program the MAX5951 switching frequency from 100kHz to 1MHz.

Choose the appropriate resistor at RT to calculate the desired output switching frequency (fsw):

 $f_{SW}(Hz) = (5 \times 10^{10}) / R_{RT}(\Omega)$

Connect an external clock (SYNCOUT from another MAX5950 or MAX5951) at SYNCIN for external clock

synchronization. For proper synchronization, the external frequency must be at least 20% higher than the frequency programmed through the RT input. If SYNCIN is 50% duty cycle, SYNCOUT is shifted by 180°, allowing the reduction of the DC-DC converter input bypass capacitor.

SYNCOUT is a synchronization signal that is used to drive the SYNCIN of a second MAX5950 or MAX5951.

Tracking (STARTUP)

The STARTUP input in conjunction with digital soft-start provides simple ratiometric tracking. When using multiple MAX5950s or MAX5951s, in addition to connecting SYNCIN and SYNCOUT signals appropriately, connect the STARTUP of all the devices together. STARTUP synchonizes the soft-start of all the devices' references, and hence their respective output voltages track ratiometrically. See Figure 1 and the *Typical Operating Circuits*.

The STARTUP input has an internal $10\mu A$ pullup current, but can be driven by external logic. When using multiple converters, connect the STARTUP of all the devices together.

Startup Sequencing (DCENI, THRESH)

The DCENI input must be above VTHRESH for the PWM controller to start. By connecting the DCENI inputs of multiple devices together and having different start thresholds (VTHRESH_), the startup of the PWM controllers can be staggered to provide power sequencing. Connect a resistive divider from REG to THRESH to AGND to set the start thresholds of each device. Connect THRESH to AGND to produce a default 1.220V threshold for DCENI. See Figure 1 and the Typical Operating Circuits.

Power-Good Sequencing (PGOOD, SENSE)

The PGOOD outputs and DCENI inputs can be daisy-chained to generate power sequencing. The PGOOD output is pulled high when the voltage at SENSE is above V_{REF} (800mV, typ). Connect a resistive divider from the power-supply output voltage to SENSE to AGND to set the power-good threshold. See Figure 1 and the *Typical Operating Circuits*.

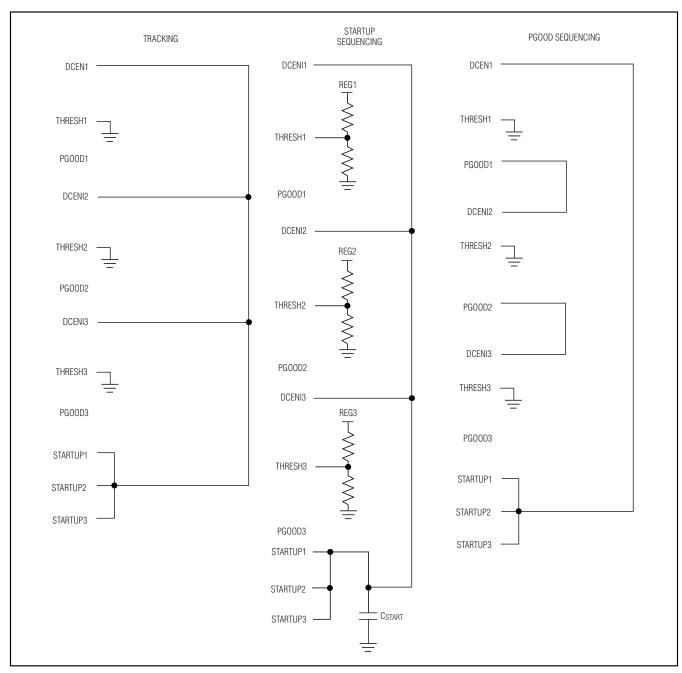


Figure 1. Tracking, STARTUP Sequencing, and PGOOD Sequencing Configurations

Error Amplifier

The output of the internal error amplifier (COMP) is available for frequency compensation (see the *Compensation Design Guidelines* section). The inverting input is FB; the output is COMP. The error amplifier has an 80dB open-loop gain and a 2.5MHz GBW product. See the *Typical Operating Characteristics* for the Open-Loop Gain and Phase vs. Frequency graph.

PWM Comparator

An internal ramp is compared against the output of the error amplifier to generate the PWM signal. The amplitude of the ramp, V_{RAMP}, is 1.8V.

Output Short-Circuit Protection (Hiccup Mode)

The current-limit circuit employs a lossless valley current-limiting algorithm that uses the MOSFET's on-resistance as the current-sensing element. Once the high-side MOSFET turns off, the voltage across the low-side MOSFET is monitored. If the voltage across the low-side MOSFET (RDS(ON) x INDUCTOR) does not exceed the current-limit threshold, the high-side MOSFET turns on normally at the start of the next cycle. If the voltage across the low-side MOSFET exceeds the current-limit threshold just before the beginning of a new PWM cycle, the controller skips that cycle. During severe overload or short-circuit conditions, the switching frequency of the device appears to decrease because the on-time of the low-side MOSFET extends beyond a clock cycle.

If the current-limit threshold is exceeded for eight cumulative clock cycles (N_{CL}), the device shuts down (both DH and DL are pulled low) for 512 clock cycles (hiccup timeout) and restarts with a soft-start sequence. If three consecutive cycles pass without a current-limit event, the

count of N_{CL} is cleared (see Figure 2). Hiccup mode protects against continuous output short circuit.

Thermal-Overload Protection

The MAX5951 features an integrated thermal-overload protection with temperature hysteresis. Thermal-overload protection limits the total power dissipation in the device and protects it in the event of an extended thermal fault condition. When the die temperature exceeds +135°C, an internal thermal sensor shuts down the device, turning off the power MOSFETs and allowing the die to cool. After the die temperature falls by +15°C, the part restarts with a soft-start sequence.

PWM Controller Design Procedures

Setting the Undervoltage Lockout

Connect an external resistive divider from IN to PUVLO to AGND to override the internal PWM UVLO divider. The rising threshold at PUVLO is set to 1.220V with 120mV hysteresis. First select the PUVLO to AGND resistor (R2), then calculate the resistor from IN to PUVLO (R1) using the following equation:

$$R1 = R2 \times \left[\frac{V_{IN}}{V_{PUVLO}} - 1 \right]$$

where V_{IN} is the input voltage at which the converter needs to turn on, $V_{PUVLO} = 1.220V$, and R2 is chosen to be less than $20k\Omega$. See Figure 3.

Leave PUVLO unconnected for the default PWM UVLO threshold. In this case, an internal voltage-divider monitors the supply voltage at IN and allows startup when IN rises above 7V (typ).

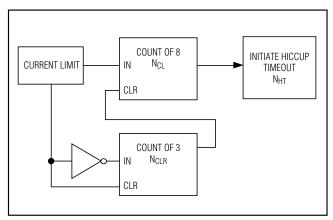


Figure 2. Hiccup Block Diagram

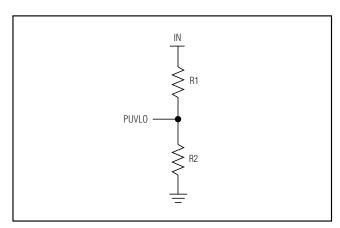


Figure 3. External PWM UVLO Divider

MIXIM

Setting the Output Voltage

Connect a resistive divider from OUT to FB to AGND to set the output voltage. First, calculate the resistor from OUT to FB using the guidelines in the *Compensation Design Guidelines* section. Once R3 is known, calculate R4 using the following equation:

$$R4 = \frac{R3}{\left[\frac{V_{OUT}}{V_{FB}} - 1\right]}$$

where $V_{FB} = 0.8V$.

Inductor Selection

Three key inductor parameters must be specified for operation with the MAX5951: inductance value (L), peak inductor current (IPEAK), and inductor saturation current (ISAT). The minimum required inductance is a function of operating frequency, input-to-output voltage differential, and the peak-to-peak inductor current (ΔIP-P). Higher ΔIP-P allows for a lower inductor value. A lower inductance value minimizes size and cost and improves largesignal and transient response, but reduces efficiency due to higher peak currents and higher peak-to-peak output voltage ripple for the same output capacitor. A higher inductance increases efficiency by reducing the ripple current; however, resistive losses due to extra wire turns can exceed the benefit gained from lower ripple current levels especially when the inductance is increased without also allowing for larger inductor dimensions. A good rule of thumb is to choose ΔI_{P-P} egual to 30% of the full-load current. Calculate the inductor using the following equation:

$$L = \frac{V_{OUT}(V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_{P-P}}$$

V_{IN} and V_{OUT} are typical values so that efficiency is optimum for typical conditions. The switching frequency is programmable between 100kHz and 1000kHz (see the *Oscillator/Synchronization Input (SYNCIN)/Synchronization Output (SYNCOUT)* section). The peak-to-peak inductor current, which reflects the peak-to-peak output ripple, is worst at the maximum input voltage. See the output capacitor selection section to verify that the worst-case output current ripple is acceptable. The inductor saturation current (ISAT) is also important to avoid runaway current during continuous output short-circuit conditions. Select an inductor with an ISAT specification higher than the maximum peak current.

Input Capacitor Selection

The discontinuous input current of the buck converter causes large input ripple currents; therefore, the input capacitor must be carefully chosen to withstand the input ripple current and maintain the input voltage ripple within design requirements. The total voltage ripple is the sum of ΔV_Q (caused by the capacitor discharge) and $\Delta V_{\rm ESR}$ (caused by the ESR of the input capacitor), which peaks at the end of the on cycle. Calculate the input capacitance and ESR required for a specified ripple using the following equations:

$$\begin{aligned} \text{ESR} &= \frac{\Delta V_{\text{ESR}}}{\left(I_{\text{LOAD(MAX)}} + \frac{\Delta I_{P-P}}{2}\right)} \\ C_{\text{IN}} &= \frac{I_{\text{LOAD(MAX)}} \times \left(\frac{V_{\text{OUT}}}{V_{\text{IN}}}\right)}{\Delta V_{\text{O}} \times f_{\text{SW}}} \end{aligned}$$

where

$$\Delta I_{P-P} = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN} \times f_{SW} \times L}$$

 $I_{LOAD(MAX)}$ is the maximum output current, ΔI_{P-P} is the peak-to-peak inductor current, and f_{SW} is the switching frequency.

The MAX5951 includes UVLO hysteresis to avoid possible unintentional chattering during turn-on. Use additional bulk capacitance if the input source impedance is high. When the input voltage is near the UVLO, additional input capacitance helps avoid possible undershoot below the UVLO threshold during transient loading.

Output Capacitor Selection

The allowed output-voltage ripple and the maximum deviation of the output voltage during load steps determine the required output capacitance and its ESR. The output ripple is mainly composed of ΔV_Q (caused by the capacitor discharge) and ΔV_{ESR} (caused by the voltage drop across the ESR of the output capacitor). The equations for calculating the peak-to-peak output-voltage ripple are:

$$\Delta V_{Q} = \frac{\Delta I_{P-P}}{8 \times C_{OUT} \times f_{SW}}$$
$$\Delta V_{ESR} = ESR \times \frac{\Delta I_{P-P}}{2}$$

 ΔV_{ESR} and ΔV_Q are not directly additive since they are out of phase from each other. If using ceramic capacitors, which generally have low ESR, ΔV_Q dominates. If using electrolytic capacitors, ΔV_{ESR} dominates.

The allowable deviation of the output voltage during load transients also affects the choice of capacitance. its ESR, and its equivalent series inductance (ESL). The output capacitor supplies the load current during a load step until the controller responds with a greater duty cycle. The response time (tresponse) depends on the closed-loop bandwidth of the converter (see the Compensation Design Guidelines section). The resistive drop across the output capacitor's ESR, the drop across the capacitor's ESL, and the capacitor discharge cause a voltage droop during the load-step. Use a combination of low-ESR tantalum/aluminum electrolyte and ceramic capacitors for better load transient and voltage ripple performance. Surface-mount capacitors and capacitors in parallel help reduce the ESL. Keep maximum output-voltage deviation below the tolerable limits of the electronics being powered. Use the following equations to calculate the required ESR, ESL, and capacitance value during a load step:

$$ESR = \frac{\Delta V_{ESR}}{|_{STEP}}$$

$$C_{OUT} = \frac{|_{STEP} \times t_{RESPONSE}}{\Delta V_{Q}}$$

$$ESL = \frac{\Delta V_{ESL} \times t_{STEP}}{|_{STEP}}$$

where ISTEP is the load step, tSTEP is the rise time of the load step, and tRESPONSE is the response time of the controller.

Setting the Current Limit

Connect a $25k\Omega$ to $175k\Omega$ resistor, R_{ILIM} , from ILIM to AGND to program the valley current-limit threshold between 50mV and 350mV. ILIM sources $20\mu A$ out to R_{ILIM} . The resulting voltage divided by 10 is the valley current-limit threshold.

The MAX5951 uses a valley current-sense method for current limiting. The voltage drop across the low-side MOSFET due to its on-resistance is used to sense the inductor current. The voltage drop across the low-side MOSFET at the valley point and at I_{LOAD(MAX)} is:

$$V_{VALLEY} = R_{DS(ON)}(T) \times \left(I_{LOAD(MAX)} - \frac{\Delta I_{P-P}}{2}\right)$$

RDS(ON) is the on-resistance of the low-side MOSFET, which is temperature dependent, $I_{LOAD(MAX)}$ is the maximum DC load current, and ΔI_{P-P} is the peak-to-peak inductor current.

The 20µA current source, ILIM reference current, has a temperature coefficient of 3333ppm/°C. This allows the valley current-limit threshold:

$$\frac{R_{ILIM} \times 20 \mu A(T)}{10}$$

to track and compensate for the increase in the synchronous MOSFET's RDS(ON) with increasing temperature. MOSFETs typically have a temperature coefficient range within 3000ppm/°C to 7000ppm/°C. Refer to the MOSFET data sheet for a device-specific temperature coefficient.

At a given temperature, the calculated V_{VALLEY} must be less than the minimum valley current-limit threshold specified.

Figure 4 illustrates the effect of MAX5951 ILIM reference current temperature coefficient to compensate for the variation of the MOSFET RDS(ON) over the operating junction temperature range.

Power MOSFET Selection

When selecting the MOSFETs, consider the total gate charge, RDS(ON), power dissipation, the maximum drain-to-source voltage, package thermal impedance, and desired current limit. The product of the MOSFET gate charge and on-resistance is a figure of merit, with a lower number signifying better performance. Choose MOSFETs optimized for high-frequency switching applications. The average gate-drive current from the MAX5951's output is proportional to the frequency and gate charge required to drive the MOSFET. The power dissipated in the MAX5951 is proportional to the input voltage and the average drive current (see the *Power Dissipation* section).

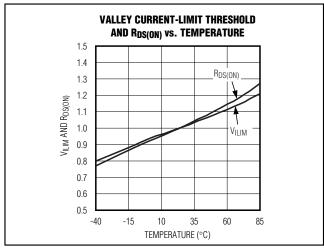


Figure 4. Current-Limit Threshold and RDS(ON) vs. Temperature

Compensation Design Guidelines

The MAX5951 uses a voltage-mode control scheme that regulates the output voltage by comparing the error amplifier output (COMP) with an internal ramp to produce the required duty cycle. The output lowpass LC filter creates a double pole at the resonant frequency, which has a gain drop of -40dB/decade. The compensation network must compensate for this gain drop and phase shift in order to achieve a stable closed-loop system.

The basic regulator loop consists of a power modulator, an output feedback divider, and a voltage-error amplifier. The power modulator has a DC gain set by V_{IN}/V_{RAMP}, with a double pole and a single zero set by the output inductance (L), the output capacitance (C_{OUT}), and its equivalent series resistance (ESR). Below are equations that define the power modulator:

$$\begin{split} G_{MOD(DC)} &= \frac{V_{IN}}{V_{RAMP}} \\ f_{LC} &= \frac{1}{2\pi\sqrt{L \times C_{OUT}}} \\ f_{ZESR} &= \frac{1}{2\pi \times C_{OUT} \times R_{ESR}} \end{split}$$

GAIN (dB)

CCB
R5
C7
R5
C7
COMP
REF
FA
COMP

CLOSED-LOOP
GAIN
EA
GAIN
FREQUENCY

Figure 5. Error-Amplifier Compensation Circuit (Closed-Loop and Error-Amplifier Gain Plot) for Ceramic Capacitors

The switching frequency is programmable between 100kHz and 1000kHz by an external resistor at RT. The crossover frequency (fc), which is the frequency when the closed-loop gain is equal to unity, should be set to fsw / 10 or fgBw / 25, whichever is lower.

The error amplifier must provide a gain-and-phase boost to compensate for the rapid gain-and-phase loss from the LC double pole. This is accomplished by utilizing type 3 compensation (see Figures 5 and 6) that introduces two zeros and three poles into the control loop. The error amplifier has a low-frequency pole (fP1) at the origin; two zeros at:

$$f_{Z1} = \frac{1}{2\pi \times R5 \times C7}$$

and:

$$f_{Z2} = \frac{1}{2\pi \times R3 \times C6}$$

and higher frequency poles at:

$$f_{P2} = \frac{1}{2\pi \times R6 \times C6}$$

and:

$$f_{P3} = \frac{1}{2\pi \times R5 \times C8}$$

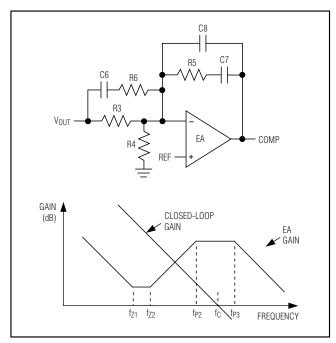


Figure 6. Error-Amplifier Compensation Circuit (Closed-Loop and Error-Amplifier Gain Plot) for Higher ESR Output Capacitors

Compensation when fc < fzesr

Figure 5 shows the error-amplifier feedback, as well as its gain response for circuits that use low-ESR output capacitors (ceramic). In this case, fc occurs before fzesr.

fz₁ is set to 0.5 x f_{LC} and fz₂ is set to f_{LC} in order to compensate for the gain-and-phase loss due to the double pole. Choose the inductor (L) and output capacitor (C_{OUT}) as described in the *Inductor Selection* and *Output Capacitor Selection* sections.

Pick a value for the feedback resistor R5 in Figure 5 (values between $1k\Omega$ and $10k\Omega$ are adequate). C7 is then calculated as:

$$C7 = \frac{1}{2\pi \times 0.5 \times f_{1,C} \times R5}$$

 $f_{\rm C}$ occurs between $f_{\rm Z2}$ and $f_{\rm P2}$. The circuit is implemented with C7 >> C8 and R3 >> R6, in which case, the error amplifier gain (GEA) at $f_{\rm C}$ is due primarily to C6 and R5. Therefore:

$$G_{EA(fc)} = 2\pi \times f_C \times C6 \times R5$$

The modulator gain at fc is:

$$G_{MOD(fC)} = \frac{G_{MOD(DC)}}{(2\pi)^2 \times L \times C_{OUT} \times f_C^2}$$

Since $GEA(fC) \times GMOD(fC) = 1$, C6 is calculated by:

$$C6 = \frac{f_C \times L \times C_{OUT} \times 2\pi}{R5 \times G_{MOD(DC)}}$$

R3 is then calculated as:

$$R3 \approx \frac{1}{2\pi \times f_{LC} \times C6}$$

fp2 is set at 1/2 the switching frequency (fsw). R6 is then calculated by:

$$R6 = \frac{1}{2\pi \times C6 \times 0.5 \times f_{SW}}$$

fp3 is set at 5 x fc. Therefore, C8 is calculated as:

$$C8 = \frac{1}{2\pi \times R5 \times 5 \times f_{C}}$$

Compensation when fc > fzesr

For larger ESR capacitors such as tantalum and aluminum electrolytic, fzesr can occur before fc. If fc > fzesr, then fc occurs between fp2 and fp3. fz1 and fz2 remain the same as before; however, fp2 is now set equal to fzesr. The output capacitor's ESR zero frequency is higher than flc but lower than the closed-loop crossover frequency. The equations that define the error amplifier's poles and zeros (fz1, fz2, fp1, fp2, and fp3) are the same as before. However, fp2 is now lower than the closed-loop crossover frequency. Figure 5 shows the error-amplifier feedback, as well as its gain response for circuits that use higher ESR output capacitors (tantalum, aluminum electrolytic, etc.).

Pick a value for feedback resistor R5 in Figure 5 (values between $1k\Omega$ and $10k\Omega$ are adequate). C7 is then calculated as:

$$C7 = \frac{1}{2\pi \times 0.5 \times f_{LC} \times R5}$$

The circuit is implemented with C7 >> C8 and R3 >> R6, in which case the error-amplifier gain between fp2 and fp3 is approximately equal to:

The modulator gain at fc is:

$$G_{MOD(fC)} = \frac{G_{MOD(DC)}}{(2\pi)^2 \times L \times C_{OUT} \times f_C^2}$$

Since $GEA(fC) \times GMOD(fC) = 1$, R6 can then be calculated as:

$$R6 \approx \frac{R5 \times G_{MOD(DC)}}{(2\pi)^2 \times L \times C_{OUT} \times f_C^2}$$

fp2 is set to fzesr. C6 is then calculated as:

$$C6 = \frac{C_{OUT} \times ESR}{R6}$$

R3 is then calculated as:

$$R3 \approx \frac{1}{2\pi \times \int_{C} \times C6}$$

f_{P3} is set at 5 x f_C. Therefore, C8 is calculated as:

$$C8 = \frac{1}{2\pi \times R5 \times 5 \times f_{C}}$$

PWM Controller Applications Information

Power Dissipation

The 32-pin TQFN thermally enhanced package can dissipate 2.7W. Calculate power dissipation in the MAX5951 as a product of the input voltage and the total REG output current (IREG). IREG includes quiescent current (IQ) and gate drive current (IDREG):

$$I_{REG} = I_{Q} + [f_{SW} \times (Q_{G1} + Q_{G2})]$$

where Q_{G1} and Q_{G2} are the total gate charge of the low-side and high-side external MOSFETs. f_{SW} is the switching frequency of the converter, and I_Q is the quiescent current of the device at the switching frequency.

Use the following equation to calculate the maximum power dissipation (P_{DMAX}) in the chip at a given ambient temperature (T_A):

 $P_{DMAX} = 34.5 \times (150 - T_{A})$

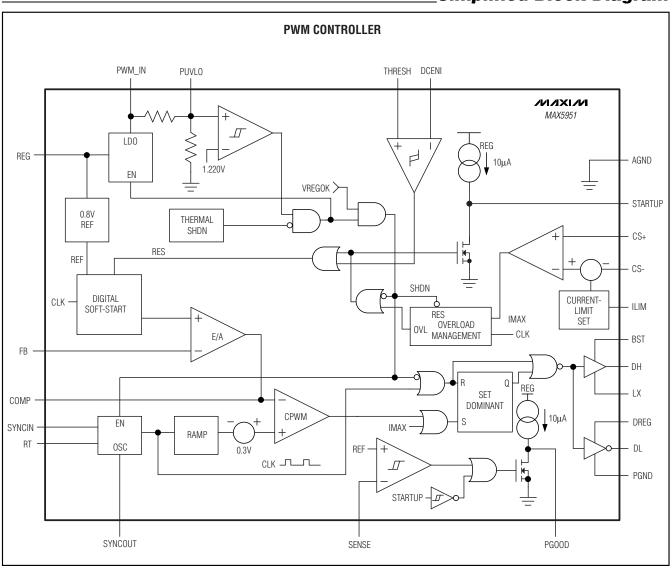
PC Board Layout Guidelines

Use the following guidelines to lay out the switching voltage regulator:

- Place the IN and DREG bypass capacitors close to the MAX5951 PGND pin. Place the REG bypass capacitor close to the AGND pin.
- Minimize the area and length of the high-current loops from the input capacitor, upper switching MOSFET, inductor, and output capacitor back to the input capacitor negative terminal.

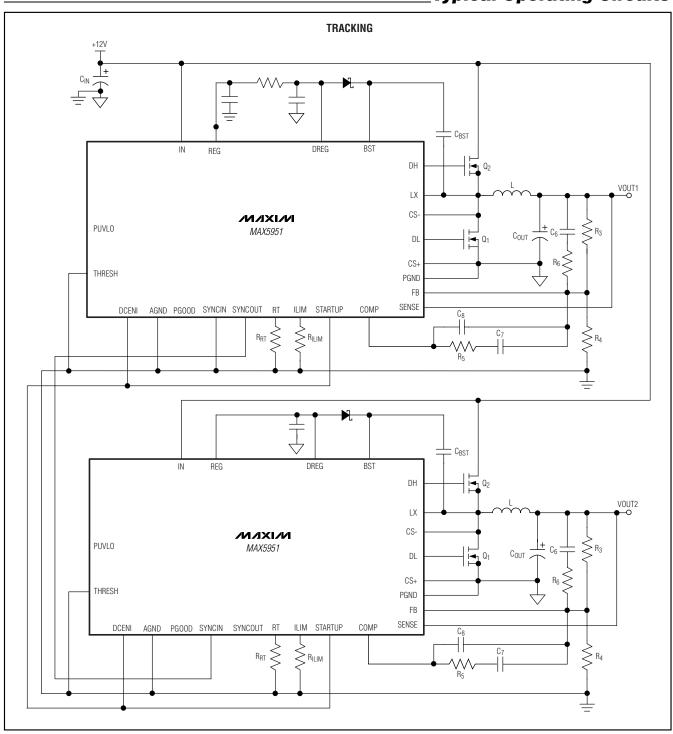
- Keep short the current loop formed by the synchronous switching MOSFET, inductor, and output capacitor.
- Keep AGND and PGND isolated and connect them at one single point close to the negative terminal of the input filter capacitor.
- 5) Run the current-sense lines CS+ and CS- close to each other to minimize the loop area.
- 6) Avoid long traces between the REG/DREG bypass capacitors, driver output of the MAX5951, MOSFET gates, and PGND. Minimize the loop formed by the REG bypass capacitors, bootstrap diode, bootstrap capacitor, the MAX5951, and the upper MOSFET gate.
- Place the bank of output capacitors close to the load.
- 8) Distribute the power components evenly across the board for proper heat dissipation.
- Provide enough copper area at and around the switching MOSFETs and inductor to aid in thermal dissipation.
- 10) Use 2oz copper to keep the trace inductance and resistance to a minimum. Thin copper PC boards can compromise efficiency since high currents are involved in the application. Also, thicker copper conducts heat more effectively, thereby reducing thermal impedance.

Simplified Block Diagram

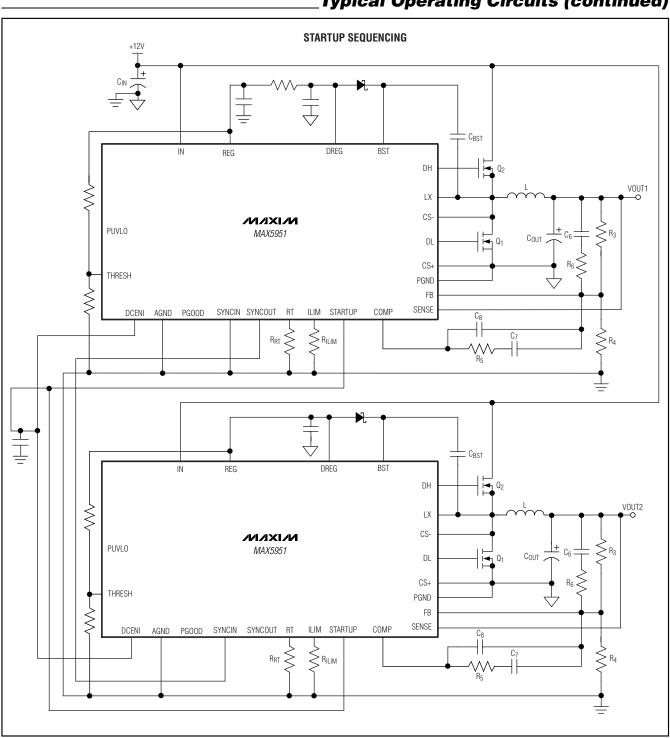


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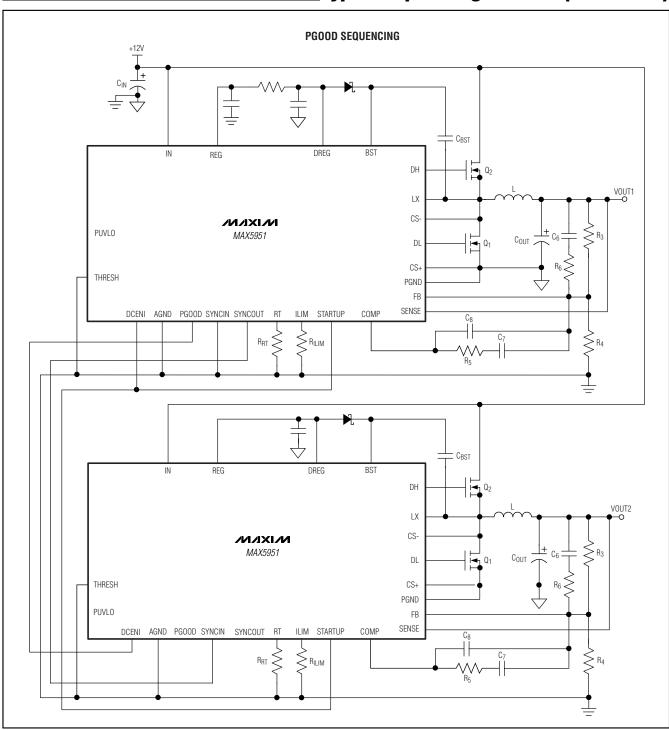
Typical Operating Circuits



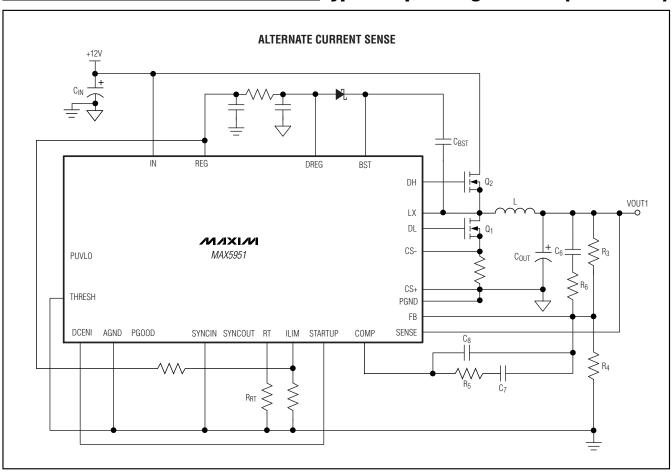
Typical Operating Circuits (continued)



Typical Operating Circuits (continued)



Typical Operating Circuits (continued)

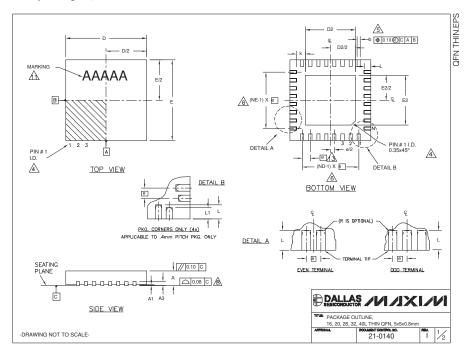


_____Chip Information

PROCESS: BICMOS

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



			C	OMM	ON D	IMEN:	SIONS	3							
PKG.	- 1	6L 5x	:5	2	0L 5	√ 5	2	8L 5>	ι5	3	2L 5>	:5	4	0L 5	κ5
SYMBOL	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX
Α	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.8
A1	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05	0	0.02	0.0
A3	0.	20 RE	F.	0.	20 RE	F.	0.	20 RE	F.	0.	20 RE	F.	0.	20 RE	F.
b	0.25	0.30	0.35	0.25	0.30	0.35	0.20	0.25	0.30	0.20	0.25	0.30	0.15	0.20	0.2
D	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.1
E	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.10	4.90	5.00	5.1
е	0	.80 B	SC.	0	.65 B	SC.	0	.50 B	SC.	0	.50 BS	SC.	0	.40 B	SC.
k	0.25	-	-	0.25	-		0.25		-	0.25	1		0.25	0.35	0.4
L	0.30	0.40	0.50	0.45	0.55	0.65	0.45	0.55	0.65	0.30	0.40	0.50	0.40	0.50	0.6
L1	-	-	-	-	-	-	-	-	-	-	-	-	0.30	0.40	0.5
N		16			20			28			32			40	
ND		4			5			7			8			10	
NE		4			5			7			8			10	
JEDEC		WHH	3		WHH	0	١	VHHD)-1	V	VHHD	-2			

NO	TES:

- 1. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14 5M-1994
- 2. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
- 3. N IS THE TOTAL NUMBER OF TERMINALS.
- $\underline{ \begin{tabular}{ll} \triangle\\ 0.25\mbox{ mm}\mbox{ APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.25\mbox{ mm}\mbox{ AND }0.30\mbox{ mm}\mbox{ FROM TERMINAL TIP.} \end{tabular}$
- AND AND NE REFER TO THE NUMBER OF TERMINALS ON EACH D AND E SIDE RESPECT DEPOPULATION IS POSSIBLE IN A SYMMETRICAL FASHION.
- (COPLANARITY APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINA DRAWING CONFORMS TO JEDEC MO220, EXCEPT EXPOSED PAD DIMENSION FOR T2855-3 AND T2855-6.
- WARPAGE SHALL NOT EXCEED 0.10 mm
- MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.
 NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.
- NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.
 LEAD CENTERLINES TO BE AT TRUE POSITION AS DEFINED BY BASIC DIMENSION "e", ±0.05.

-DRAWING NOT TO SCALE

PKG.		D2			E2		exceptions	DOWN BONDS
CODES	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	±0.15	ALLOWED
T1655-2	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
T1655-3	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
T1655N-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
T2055-3	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
T2055-4	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
T2055-5	3.15	3.25	3.35	3.15	3.25	3.35	0.40	YES
T2855-3	3.15	3.25	3.35	3.15	3.25	3.35	**	YES
T2855-4	2.60	2.70	2.80	2.60	2.70	2.80	**	YES
T2855-5	2.60	2.70	2.80	2.60	2.70	2.80	**	NO
T2855-6	3.15	3.25	3.35	3.15	3.25	3.35	**	NO
T2855-7	2.60	2.70	2.80	2.60	2.70	2.80	**	YES
T2855-8	3.15	3.25	3.35	3.15	3.25	3.35	0.40	YES
T2855N-1	3.15	3.25	3.35	3.15	3.25	3.35	**	NO
T3255-3	3.00	3.10	3.20	3 .00	3.10	3.20	**	YES
T3255-4	3.00	3.10	3.20	3 .00	3.10	3.20	**	NO
T3255-5	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
T3255N-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
T4055-1	3.20	3.30	3.40	3.20	3.30	3.40	**	YES
T4055-1	3.20	3.30	3.40			0		YES ONS TABL
Υ.								

EXPOSED PAD VARIATIONS

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

PACKAGE OUTLINE, 16, 20, 28, 32, 40L THIN QFN, 5x5x0.8